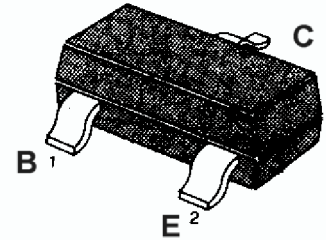


**APPLICATION:**High Voltage Switching Applications.

**MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CB0</sub>	-200	V
Collector-emitter voltage	V <sub>CEO</sub>	-200	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-50	mA
Collector Power Dissipation	P <sub>C</sub>	150	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C

**SOT-23**


1.Base 2 .Emitter 3 .Collector

**ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	70		240		V <sub>CE</sub> = -3V, I <sub>C</sub> = -1mA
Collector Cut-off Current	I <sub>CB0</sub>			-0.1	μA	V <sub>CB</sub> = -200V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			-0.1	μA	V <sub>EB</sub> = -5V, I <sub>C</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	-200			V	I <sub>C</sub> = -0.1mA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-200			V	I <sub>C</sub> = -1mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5			V	I <sub>E</sub> = -0.1mA, I <sub>C</sub> =0
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		-0.2	-1	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		-0.75	-1.5	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1mA
Gain bandwidth product	f <sub>T</sub>	50	100		MHz	I <sub>C</sub> = -2mA, V <sub>CE</sub> = -10V
Common Base Output Capacitance	C <sub>ob</sub>		3	7	PF	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f = 1MHz
Turn on Time	t <sub>on</sub>		0.3		μs	V <sub>cc</sub> = -50V, I <sub>C</sub> = -6mA, -I <sub>B1</sub> =I <sub>B2</sub> =0.5mA
Turn off Time	t <sub>off</sub>		0.4		μs	V <sub>cc</sub> = -50V, I <sub>C</sub> = -6mA, -I <sub>B1</sub> =I <sub>B2</sub> =0.5mA

**h<sub>FE</sub> Classification And Marking**

Print Mark	MO	MY
Classification	O	Y
h <sub>FE</sub>	70~140	120~240